

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
8 December 2005 (08.12.2005)

PCT

(10) International Publication Number  
**WO 2005/117079 A1**

(51) International Patent Classification<sup>7</sup>: **H01L 21/208**,  
C01B 33/02, C30B 19/10, 29/06, H01L 31/04

(21) International Application Number:  
PCT/JP2005/009305

(22) International Filing Date: 17 May 2005 (17.05.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:  
2004-156968 27 May 2004 (27.05.2004) JP

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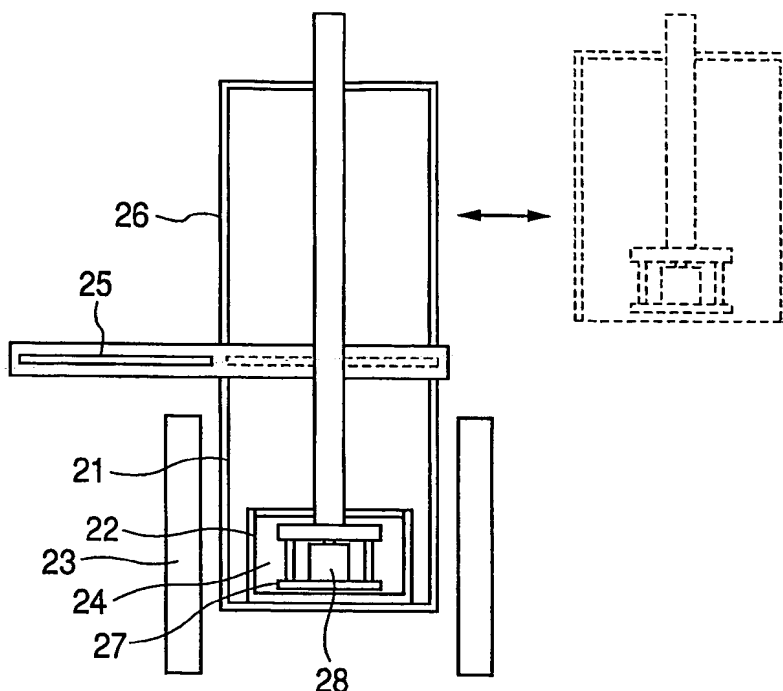
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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KM, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO,

[Continued on next page]

(54) Title: SILICON LAYER PRODUCTION METHOD AND SOLAR CELL PRODUCTION METHOD



(57) Abstract: A solar cell is produced by dipping a multicrystalline silicon substrate 28 in a solution 24 containing silicon, growing a silicon layer on the substrate 28 while decreasing with time the temperature drop rate of the solution during the dipping of the substrate in the solution, and forming a pn junction in the silicon layer. Thereby, there is provided a silicon layer production method that can form a thick layer while restraining the degree of roughness, whereby a low-cost, multicrystalline-silicon solar cell production method is provided that realizes both a large current and a high FF.



SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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**Published:**

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